NSN 5961-01-176-6655

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View Online at https://aerobasegroup.com/nsn/5961-01-176-6655 **Inclosure Material:** Metal **Overall Length:** 1.573 inches **Overall Height:** 0.380 inches **Overall Width:** 1.050 inches **Mounting Facility Quantity: Internal Configuration:** Field effect Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-3 **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case and quality assurance level tx **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 400.0 drain to source voltage and 400.0 drain to gate voltage **Current Rating Per Characteristic:** 5.50 amperes source current and 8.00 amperes off-state current, peak **Power Rating Per Characteristic:** 75.0 watts total power dissipation **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 pin and 1 case **Specification Data:** 81349-mil-s-19500/542 government specification Shelf Life: N/a **Unit Of Measure:**

No Fiig:

A110a0

Demilitarization: